

L Number	Hits	Search Text	DB	Time stamp
1	1175	radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5	USPAT; EPO; JPO; DERWENT	2002/12/08 12:17
2	34	radiat\$3 same amorphous same silicon same dop\$3 same crystalliz\$5	USPAT; EPO; JPO; DERWENT	2002/12/08 12:12
3	12	(radiat\$3 same amorphous same silicon same dop\$3 same crystalliz\$5) same gate	USPAT; EPO; JPO; DERWENT	2002/12/08 12:12
4	350	radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5 and (gate with dop\$3)	USPAT; EPO; JPO; DERWENT	2002/12/08 12:22
5	315	(radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5 and (gate with dop\$3)) and laser	USPAT; EPO; JPO; DERWENT	2002/12/08 12:20
6	181	((radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5 and (gate with dop\$3)) and laser) and 438/\$3.ccls.	USPAT; EPO; JPO; DERWENT	2002/12/08 12:21
7	181	((radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5 and (gate with dop\$3)) and laser) and 438/\$3.ccls.) and @ad<20010829	USPAT; EPO; JPO; DERWENT	2002/12/08 12:21
8	33	radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5 and (gate with dop\$3 with amorphous)	USPAT; EPO; JPO; DERWENT	2002/12/08 12:59
9	4	radiat\$3 and (crystalliz\$5 with gate with dop\$3 with amorphous)	USPAT; EPO; JPO; DERWENT	2002/12/08 13:04
10	2	radiat\$3 same amorphous same (crystalliz\$5 with gate with dop\$3)	USPAT; EPO; JPO; DERWENT	2002/12/08 13:08
11	11	radiat\$3 same amorphous same crystalliz\$5 same (gate with dop\$3)	USPAT; EPO; JPO; DERWENT	2002/12/08 13:30
12	28	anneal\$3 same crystalliz\$5 same (amorphous with gate with dop\$3)	USPAT; EPO; JPO; DERWENT	2002/12/08 15:51
13	3	("5872761" "5994179" "6054355").PN.	USPAT	2002/12/08 14:00
14	11	gate with height with "500" with (nanometer\$1 or nm)	USPAT; EPO; JPO; DERWENT	2002/12/08 15:55
15	62	gate with height with ("400" or "300" or "200" or "100") with (nanometer\$1 or nm)	USPAT; EPO; JPO; DERWENT	2002/12/08 15:56
-	213204	257/\$3.ccls. or 438/\$3.ccls.	USPAT; EPO; JPO; DERWENT	2002/12/08 11:42
-	6	(257/\$3.ccls. or 438/\$3.ccls.) and insulat\$3 and radiat\$3 and (amorphous near2 silicon) and crystall\$7 and explosive	USPAT; EPO; JPO; DERWENT	2002/04/09 09:46
-	1	(257/\$3.ccls. or 438/\$3.ccls.) and (xcr or (explosive adj recrystallization)) and irradiat\$3 and dopant and gate	USPAT; EPO; JPO; DERWENT	2002/04/09 09:58
-	103	(257/\$3.ccls. or 438/\$3.ccls.) and recrystallization and irradiat\$3 and dopant and gate	USPAT; EPO; JPO; DERWENT	2002/04/09 09:59
-	85	((257/\$3.ccls. or 438/\$3.ccls.) and recrystallization and irradiat\$3 and dopant and gate) and (amorphous adj silicon)	USPAT; EPO; JPO; DERWENT	2002/04/09 15:19
-	3	mosfet same (laser or irradiate) same amorphous same (dopant or dope)	USPAT; EPO; JPO; DERWENT	2002/04/09 16:11
-	111	(laser or irradiate) same (amorphous adj silicon) same (dopant or dope)	USPAT; EPO; JPO; DERWENT	2002/04/10 16:52
-	10	((laser or irradiate) same (amorphous adj silicon) same (dopant or dope)) same (insulat\$4 adj layer)	USPAT; EPO; JPO; DERWENT	2002/04/09 16:14

-	241	mosfet with laser	USPAT; EPO; JPO; DERWENT	2002/04/09 17:50
-	2	(mosfet with laser) same (amorphous adj silicon)	USPAT; EPO; JPO; DERWENT	2002/04/09 17:52
-	12	(mosfet with laser) same (dope dopant doped)	USPAT; EPO; JPO; DERWENT	2002/04/09 18:06
-	42	(mosfet with laser) and ((dope dopant doped) with gate)	USPAT; EPO; JPO; DERWENT	2002/04/09 18:07
-	12557	(mosfet or fet or mos) same dop\$3 same gate	USPAT; EPO; JPO; DERWENT	2002/04/10 17:18
-	158	((mosfet or fet or mos) same dop\$3 same gate) same (laser or irradiation)	USPAT; EPO; JPO; DERWENT	2002/04/10 11:07
-	4	"5966605"	USPAT; EPO; JPO; DERWENT	2002/04/10 11:07
-	54793	gate with silicon	USPAT; EPO; JPO; DERWENT	2002/04/10 14:12
-	6957	((mosfet or fet or mos) same dop\$3 same gate) and (gate with silicon)	USPAT; EPO; JPO; DERWENT	2002/04/10 14:12
-	15744	gate near2 silicon	USPAT; EPO; JPO; DERWENT	2002/04/10 14:12
-	2731	((mosfet or fet or mos) same dop\$3 same gate) and (gate near2 silicon)	USPAT; EPO; JPO; DERWENT	2002/04/10 14:12
-	234	((mosfet or fet or mos) same dop\$3 same gate) and (gate near2 silicon)) and (laser or irradiate)	USPAT; EPO; JPO; DERWENT	2002/04/10 14:15
-	110	((mosfet or fet or mos) same dop\$3 same gate) and (gate near2 silicon)) and (laser or irradiate)) and amorphous and (recrystallize or polycrystalline or crystalline)	USPAT; EPO; JPO; DERWENT	2002/04/10 16:15
-	13	"5937325"	USPAT; EPO; JPO; DERWENT	2002/04/10 16:19
-	8	"6013928"	USPAT; EPO; JPO; DERWENT	2002/04/10 16:20
-	34	(laser or irradiate) same (amorphous adj silicon) same ((dopant or dope) and (sputter or deposition or evaporation))	USPAT; EPO; JPO; DERWENT	2002/04/10 16:53
-	3488	(mosfet or fet or mos) same dop\$3 same gate same (sputter or evaporat\$3 or deposit\$3)	USPAT; EPO; JPO; DERWENT	2002/04/10 17:20
-	3958	((mosfet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or deposit\$3 or evaporat\$3))	USPAT; EPO; JPO; DERWENT	2002/04/10 17:21
-	137	((mosfet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or evaporat\$3))	USPAT; EPO; JPO; DERWENT	2002/04/10 17:21
-	41	((mosfet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter or evaporat\$3))	USPAT; EPO; JPO; DERWENT	2002/04/10 17:25
-	75	((mosfet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3))	USPAT; EPO; JPO; DERWENT	2002/04/10 17:32
-	320	(dop\$3 with (sputter\$3 or evaporat\$3) with silicon) and (mos or fet or mosfet)	USPAT; EPO; JPO; DERWENT	2002/04/10 17:46
-	35	(dop\$3 with (sputter\$3 or evaporat\$3) with silicon) same (mos or fet or mosfet)	USPAT; EPO; JPO; DERWENT	2002/04/10 17:35

-	28	(dop\$3 with (sputter\$3 or evaporat\$3) with silicon) same laser	USPAT; EPO; JPO; DERWENT	2002/04/10 17:51
-	190	(dop\$3 with (sputter\$3 or evaporat\$3)) same laser	USPAT; EPO; JPO; DERWENT	2002/04/10 18:02
-	2	"6165875"	USPAT; EPO; JPO; DERWENT	2002/04/10 18:02
-	2848	gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)	USPAT; EPO; JPO; DERWENT	2002/04/11 16:14
-	331	(gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser	USPAT; EPO; JPO; DERWENT	2002/04/11 16:20
-	89	(gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser and mosfet	USPAT; EPO; JPO; DERWENT	2002/04/11 16:20
-	4	"6077758"	USPAT; JPO; DERWENT	2002/04/11 17:34
-	11867	(boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)	USPAT; EPO; JPO; DERWENT	2002/04/15 14:06
-	12	((boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)) same dopant same laser	USPAT; EPO; JPO; DERWENT	2002/04/15 14:02
-	1098	((boron or indium or arsenic or phosphorus) near2 layer) with (sputter\$3 or CVD or evaporat\$3)	USPAT; EPO; JPO; DERWENT	2002/04/15 15:10
-	33	((boron or indium or arsenic or phosphorus) near2 layer) with (sputter\$3 or CVD or evaporat\$3)) same dopant	USPAT; EPO; JPO; DERWENT	2002/04/15 14:09
-	239	((boron or indium or arsenic or phosphorus) near2 layer) with (sputter\$3 or CVD or evaporat\$3) with surface	USPAT; EPO; JPO; DERWENT	2002/04/15 15:13
-	46	((boron or indium or arsenic or phosphorus) near2 layer) with (sputter\$3 or CVD or evaporat\$3) with surface) and laser	USPAT; EPO; JPO; DERWENT	2002/04/15 15:14
-	2	5966605.pn.	USPAT; EPO; JPO; DERWENT	2002/09/13 13:14
-	2	6365476.pn.	USPAT; EPO; JPO; DERWENT	2002/09/13 13:15
-	2	6274488.pn.	USPAT; EPO; JPO; DERWENT	2002/09/13 13:16
-	2	6077758.pn.	USPAT; EPO; JPO; DERWENT	2002/09/13 13:16